2SA0885 (2SA885)

Silicon PNP epitaxial planar type

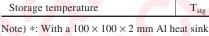
For low-frequency power amplification Complementary to 2SC1846

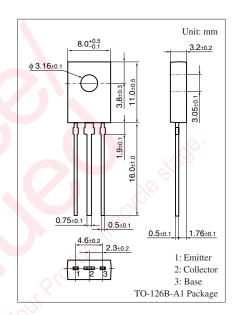
■ Features

- Output of 3 W can be obtained by a complementary pair with 2SC1846
- TO-126B package which requires no insulation plate for installation to the heat sink

■ Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	-45	V
Collector-emitter voltage (Base open)	V _{CEO}	-35	V
Emitter-base voltage (Collector open)	V_{EBO}	-5	V
Collector current	I_{C}	-1	A
Peak collector current	I_{CP}	-1.5	A
Collector power dissipation	P _C	1.2	W
		5.0 *	10
Junction temperature	T_{j}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C×(





■ Electrical Characteristics $T_a = 25$ °C ± 3 °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_{\rm C} = -10 \mu\text{A}, I_{\rm E} = 0$	-45			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = -2 \text{ mA}, I_{\rm B} = 0$				V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -20 \text{ V}, I_E = 0$			- 0.1	μΑ
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CE} = -20 \text{ V}, I_{B} = 0$			-100	μΑ
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = -5 \text{ V}, I_C = 0$			-10	μΑ
Forward current transfer ratio	h _{FE1} *	$V_{CE} = -10 \text{ V}, I_{C} = -500 \text{ mA}$	85		340	_
	h _{FE2}	$V_{CE} = -5 \text{ V}, I_{C} = -1 \text{ A}$	50			_
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$			- 0.5	V
Transition frequency	f_T	$V_{CE} = -10 \text{ V}, I_E = 50 \text{ mA}, f = 200 \text{ MHz}$		200		MHz
Collector output capacitance	C _{ob}	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		20	30	pF
(Common base, input open circuited)						

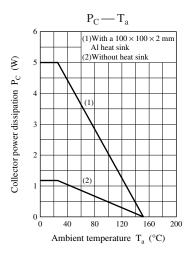
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

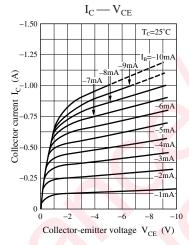
2. *: Rank classification

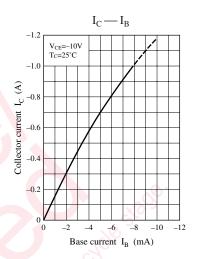
Rank	Q	R	S	
h_{FE1}	85 to 170	120 to 240	170 to 340	

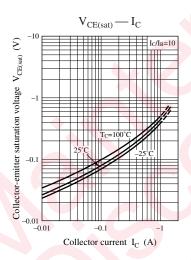
Note) The part number in the parenthesis shows conventional part number.

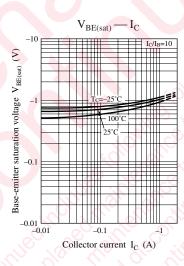
Panasonic

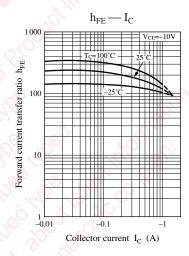


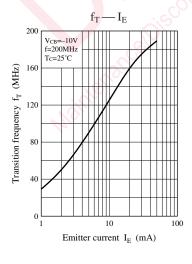


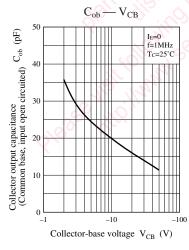


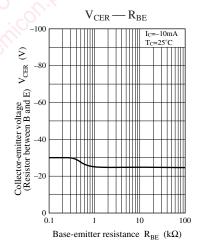




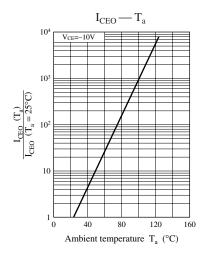


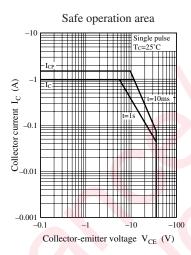






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